MCR106 scr

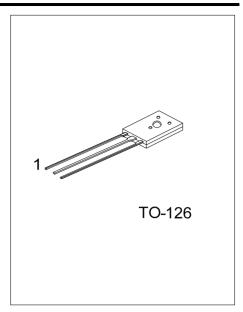
REVERSE BLOCKING TRIODE THYRISTORS

■ DESCRIPTION

PNPN devices designed for high volume consumer applications such as temperature, light and speed control; process and remote control, and warning systems where reliability of operation is important.

■ FEATURES

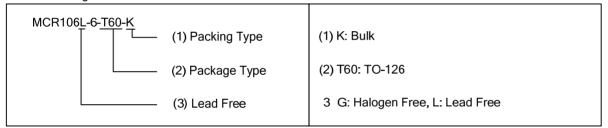
- * Glass-passivated surface for reliability and uniformity
- * Power rated at economical prices
- * Practical level triggering and holding characteristics
- * Flat, rugged, thermopad construction for low thermal resistance, high heat dissipation and durability



ORDERING INFORMATION

Ordering Number		Doolsons	Pin Assignment			Daaldaa	
Lead Free	Halogen Free	Package	1	2	3	Packing	
MCR106L-6-T60-K	MCR106G-6-T60-K	TO-126	K	Α	G	Bulk	
MCR106L-8-T60-K	MCR106G-8-T60-K	TO-126	Κ	Α	G	Bulk	

Note: Pin assignment: G: Gate K: Cathode A: Anode



■ ABSOLUTE MAXIMUM RATINGS (T_J=25°C, unless otherwise specified)

PARAMETER	SYMBOL	RATINGS	UNIT
Peak Repetitive Forward and Reverse Blocking MCR106-6	V V	400	V
Voltage (Note 1) (T_J =110°C, R_{GK} =1k Ω) MCR106-8	V_{DRM}, V_{RRM}	600	V
RMS Forward Current (All conduction Angles)	I _{T(RMS)}	4	Α
Average Forward Current (T _C =93 °C or T _A =30 °C)	I _{T(AV)}	2.55	Α
Peak Non-repetitive Surge Current (1/2 Cycle, 60Hz, T _J =-40 ~ +110 °C)	I _{TSM}	25	Α
Circuit Fusing Considerations (t=8.3 ms)	l ² t	2.6	A ² S
Peak Gate Power	P_{GM}	0.5	W
Average Gate Power	P _{G(AV)}	0.1	W
Peak Forward Gate Current	I_{GM}	0.2	Α
Peak Reversed Gate Voltage	V_{RGM}	6	V
Mounting Torque (Note 2)		6	In. lb.
Junction Temperature	T_J	+110	$^{\circ}\!\mathbb{C}$
Storage Temperature	T _{STG}	-40 ~ +150	$^{\circ}\!\mathbb{C}$

- Note 1. V_{DRM} and V_{RRM} for all types can be applied on a continuous basis. Ratings apply for zero or negative gate voltage; however, positive gate voltage shall not be applied concurrent with negative potential on the anode. Blocking voltages shall not be tested with a constant current source such that the voltage of the devices are exceeded.
 - 2. Torque rating applies with use of compression washer (B52200-F006 or equivalent). Mounting torque in excess of 6 in. lb. does not appreciably lower case-to-sink thermal resistance. Anode lead and heatsink contact pad are common. For soldering purposes (either terminal connection or device mounting), soldering temperatures shall not exceed +200℃. For optimum results, an activated flux (oxide removing) is recommended.
 - 3. Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

MCR106 scr

■ THERMAL DATA

PARAMETER	SYMBOL	RATINGS	UNIT
Junction to Ambient	θ_{JA}	75	°C/W
Junction to Case	$\theta_{ m JC}$	3	°C/W

■ ELECTRICAL CHARACTERISTICS (T_C =25 $^{\circ}$ C and R_{GK} =1000 Ω , unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Peak Forward or Reverse Blocking		T _J =25℃			10	μΑ
Current (V _{AK} =Rated V _{DRM} or V _{RRM})	I _{DRM} ,I _{RRM}	T _J =100℃			200	μА
Forward "On" Voltage (I _{TM} =4A peak)	V_{TM}				2	V
Gate Trigger Current (continuous DC)		V_{AK} =7V, R_L =100 Ω			200	
(Note)		V_{AK} =7 V , R_L =100 Ω , T_C =-40 $^{\circ}$ C			500	μΑ
Gate Trigger Voltage (continuous DC)	V_{GT}	V_{AK} =7 V , R_L =100 Ω , T_C =25 $^{\circ}$ C			1	V
Gate Non-Trigger Voltage	V_{GD}	V_{AK} =Rated V_{DRM} , R_L =100 Ω , T_J =110 $^{\circ}$ C	0.2			V
Holding Current	I _H	V _{AK} =7V, T _C =25 °C	•		5	mA
Forward Voltage Application Rate	dv/dt	T _J =110°C		10		V/μs

Note: R_{GK} current is not included in measurement.

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